Dual Precision Retriggerable/Resettable Monostable Multivibrator

MC14538B

The MC14538B is a dual, retriggerable, resettable monostable multivibrator. It may be triggered from either edge of an input pulse, and produces an accurate output pulse over a wide range of widths, the duration and accuracy of which are determined by the external timing components, C_X and R_X. Output Pulse Width T = $R_X \cdot C_X$ (secs)

R_X = Ω

C_X = Farads

Features

- Unlimited Rise and Fall Time Allowed on the A Trigger Input
- Pulse Width Range = 10 μs to 10 s
- Latched Trigger Inputs
- Separate Latched Reset Inputs
- 3.0 Vdc to 18 Vdc Operational Limits
- Triggerable from Positive (A Input) or Negative−Going Edge (B−Input)
- Capable of Driving Two Low−Power TTL Loads or One Low−Power Schottky TTL Load Over the Rated Temperature Range
- Pin−for−pin Compatible with MC14528B and CD4528B (CD4098)
- Use the MC54/74HC4538A for Pulse Widths Less Than 10 μs with Supplies Up to 6 V
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable
- These Devices are Pb−Free and are RoHS Compliant

MAXIMUM RATINGS (Voltages Referenced to V_{SS})

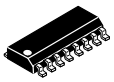
Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	−0.5 to +18.0	V
V_{in}, V_{out}	Input or Output Voltage Range (DC or Transient)	−0.5 to V_{DD} + 0.5	V
I_{in}, I_{out}	Input or Output Current (DC or Transient) per Pin	±10	mA
P_D	Power Dissipation, per Package (Note 1)	500	mW
T_A	Operating Temperature Range	−55 to +125	°C
T_{stg}	Storage Temperature Range	−65 to +150	°C
T_L	Lead Temperature (8−Second Soldering)	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

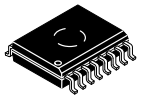
1. Temperature Derating: “D/DW” Packages: −7.0 mW/°C From 65°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high−impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \le (V_{in}$ or $V_{out}) \le V_{DD}$.

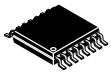
Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.



SOIC−16
D SUFFIX
CASE 751B

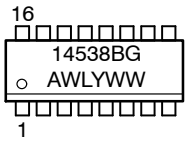


SOIC−16WB
DW SUFFIX
CASE 751G

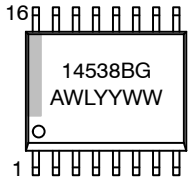


TSSOP−16
DT SUFFIX
CASE 948F

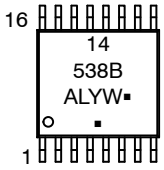
MARKING DIAGRAMS



SOIC−16



SOIC−16WB



TSSOP−16

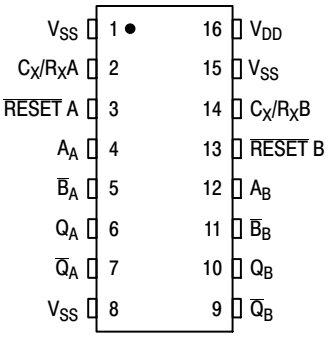
A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week
G or ▪ = Pb−Free Indicator

(Note: Microdot may be in either location)

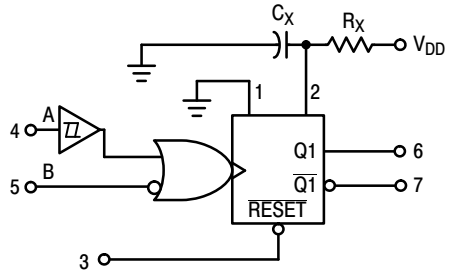
ORDERING INFORMATION

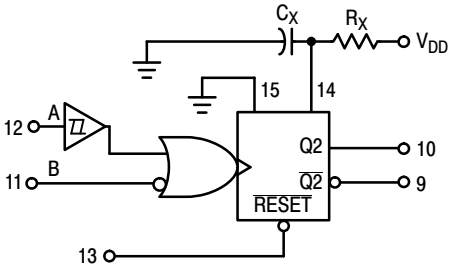
See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

PIN ASSIGNMENT



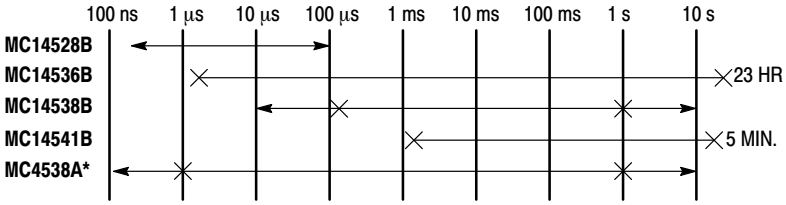
BLOCK DIAGRAM





RX AND CX ARE EXTERNAL COMPONENTS.
VDD = PIN 16
VSS = PIN 8, PIN 1, PIN 15

ONE−SHOT SELECTION GUIDE



*LIMITED OPERATING VOLTAGE (2 − 6 V)

TOTAL OUTPUT PULSE WIDTH RANGE
RECOMMENDED PULSE WIDTH RANGE

ORDERING INFORMATION

Device	Package	Shipping†
MC14538BDG	SOIC−16 (Pb−Free)	48 Units / Rail
MC14538BDR2G	SOIC−16 (Pb−Free)	2500 Units / Tape & Reel
NLV14538BDR2G*	SOIC−16 (Pb−Free)	2500 Units / Tape & Reel
MC14538BDTR2G	TSSOP−16 (Pb−Free)	2500 Units / Tape & Reel
NLV14538BDTR2G*	TSSOP−16 (Pb−Free)	2500 Units / Tape & Reel
MC14538BDWG	SOIC−16 WB (Pb−Free)	47 Units / Rail
NLV14538BDWG*	SOIC−16 WB (Pb−Free)	47 Units / Rail
MC14538BDWR2G	SOIC−16 WB (Pb−Free)	1000 Units / Tape & Reel
NLV14538BDWR2G*	SOIC−16 WB (Pb−Free)	1000 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable.

ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V_{DD} Vdc	– 55°C Min	– 55°C Max	25°C Min	25°C Typ (Note 2)	25°C Max	125°C Min	125°C Max	Unit
Output Voltage “0” Level V_{in} = V_{DD} or 0	V_{OL}	5.0 10 15	– – –	0.05 0.05 0.05	– – –	0 0 0	0.05 0.05 0.05	– – –	0.05 0.05 0.05	Vdc
“1” Level V_{in} = 0 or V_{DD}	V_{OH}	5.0 10 15	4.95 9.95 14.95	– – –	4.95 9.95 14.95	5.0 10 15	– – –	4.95 9.95 14.95	– – –	Vdc
Input Voltage “0” Level (V_O = 4.5 or 0.5 Vdc) (V_O = 9.0 or 1.0 Vdc) (V_O = 13.5 or 1.5 Vdc)	V_{IL}	5.0 10 15	– – –	1.5 3.0 4.0	– – –	2.25 4.50 6.75	1.5 3.0 4.0	– – –	1.5 3.0 4.0	Vdc
“1” Level (V_O = 0.5 or 4.5 Vdc) (V_O = 1.0 or 9.0 Vdc) (V_O = 1.5 or 13.5 Vdc)	V_{IH}	5.0 10 15	3.5 7.0 11	– – –	3.5 7.0 11	2.75 5.50 8.25	– – –	3.5 7.0 11	– – –	Vdc
Output Drive Current (V_{OH} = 2.5 Vdc) Source (V_{OH} = 4.6 Vdc) (V_{OH} = 9.5 Vdc) (V_{OH} = 13.5 Vdc)	I_{OH}	5.0 5.0 10 15	–3.0 –0.64 –1.6 –4.2	– – – –	–2.4 –0.51 –1.3 –3.4	–4.2 –0.88 –2.25 –8.8	– – – –	–1.7 –0.36 –0.9 –2.4	– – – –	mAdc
(V_{OL} = 0.4 Vdc) Sink (V_{OL} = 0.5 Vdc) (V_{OL} = 1.5 Vdc)	I_{OL}	5.0 10 15	0.64 1.6 4.2	– – –	0.51 1.3 3.4	0.88 2.25 8.8	– – –	0.36 0.9 2.4	– – –	mAdc
Input Current, Pin 2 or 14	I_{in}	15	–	±0.05	–	±0.00001	±0.05	–	±0.5	μAdc
Input Current, Other Inputs	I_{in}	15	–	±0.1	–	±0.00001	±0.1	–	±1.0	μAdc
Input Capacitance, Pin 2 or 14	C_{in}	–	–	–	–	25	–	–	–	pF
Input Capacitance, Other Inputs (V_{in} = 0)	C_{in}	–	–	–	–	5.0	7.5	–	–	pF
Quiescent Current (Per Package) Q = Low, $\overline{Q}$ = High	I_{DD}	5.0 10 15	– – –	5.0 10 20	– – –	0.005 0.010 0.015	5.0 10 20	– – –	150 300 600	μAdc
Quiescent Current, Active State (Both) (Per Package) Q = High, $\overline{Q}$ = Low	I_{DD}	5.0 10 15	– – –	2.0 2.0 2.0	– – –	0.04 0.08 0.13	0.20 0.45 0.70	– – –	2.0 2.0 2.0	mAdc
Total Supply Current at an external load capacitance (C_L) and at external timing network (R_X, C_X) (Note 3)	I_T	5.0 10	$I_T = (3.5 \times 10^{-2})\ R_X C_X f + 4 C_X f + 1 \times 10^{-5}\ C_L f$ $I_T = (8.0 \times 10^{-2})\ R_X C_X f + 9 C_X f + 2 \times 10^{-5}\ C_L f$ $I_T = (1.25 \times 10^{-1})\ R_X C_X f + 12 C_X f + 3 \times 10^{-5}\ C_L f$ where: I_T in μA (one monostable switching only), C_X in μF, C_L in pF, R_X in k ohms, and f in Hz is the input frequency.							μAdc

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.
3. The formulas given are for the typical characteristics only at 25°C.

OPERATING CONDITIONS

External Timing Resistance	R_X	–	5.0	–	(Note 4)	kΩ
External Timing Capacitance	C_X	–	0	–	No Limit (Note 5)	μF

4. The maximum usable resistance R_X is a function of the leakage of the capacitor C_X, leakage of the MC14538B, and leakage due to board layout and surface resistance. Susceptibility to externally induced noise signals may occur for R_X > 1 MΩ..
5. If C_X > 15 μF, use discharge protection diode per Fig. 11.

SWITCHING CHARACTERISTICS (Note 6) (C_L = 50 pF, T_A = 25°C)

Characteristic	Symbol	V_{DD} Vdc	All Types			Unit
			Min	Typ (Note 7)	Max	
Output Rise Time	t_{TLH}					ns
t_{TLH} = (1.35 ns/pF) C_L + 33 ns		5.0	–	100	200	
t_{TLH} = (0.60 ns/pF) C_L + 20 ns		10	–	50	100	
t_{TLH} = (0.40 ns/pF) C_L + 20 ns		15	–	40	80	
Output Fall Time	t_{THL}					ns
t_{THL} = (1.35 ns/pF) C_L + 33 ns		5.0	–	100	200	
t_{THL} = (0.60 ns/pF) C_L + 20 ns		10	–	50	100	
t_{THL} = (0.40 ns/pF) C_L + 20 ns		15	–	40	80	
Propagation Delay Time	t_{PLH},					ns
A or B to Q or $\overline{Q}$	t_{PHL}					
t_{PLH}, t_{PHL} = (0.90 ns/pF) C_L + 255 ns		5.0	–	300	600	
t_{PLH}, t_{PHL} = (0.36 ns/pF) C_L + 132 ns		10	–	150	300	
t_{PLH}, t_{PHL} = (0.26 ns/pF) C_L + 87 ns		15	–	100	220	
$\overline{Reset}$ to Q or $\overline{Q}$						ns
t_{PLH}, t_{PHL} = (0.90 ns/pF) C_L + 205 ns		5.0	–	250	500	
t_{PLH}, t_{PHL} = (0.36 ns/pF) C_L + 107 ns		10	–	125	250	
t_{PLH}, t_{PHL} = (0.26 ns/pF) C_L + 82 ns		15	–	95	190	
Input Rise and Fall Times	t_r, t_f	5	–	–	15	μs
$\overline{Reset}$		10	–	–	5	
		15	–	–	4	
B Input		5	–	300	1.0	ms
		10	–	1.2	0.1	
		15	–	0.4	0.05	
A Input		5	No Limit			–
		10				
		15				
Input Pulse Width	t_{WH},	5.0	170	85	–	ns
A, B, or Reset	t_{WL}	10	90	45	–	
		15	80	40	–	
Retrigger Time	t_{rr}	5.0	0	–	–	ns
		10	0	–	–	
		15	0	–	–	
Output Pulse Width — Q or $\overline{Q}$	T					μs
Refer to Figures 8 and 9						
C_X = 0.002 μF, R_X = 100 kΩ		5.0	198	210	230	
		10	200	212	232	
		15	202	214	234	
C_X = 0.1 μF, R_X = 100 kΩ		5.0	9.3	9.86	10.5	ms
		10	9.4	10	10.6	
		15	9.5	10.14	10.7	
C_X = 10 μF, R_X = 100 kΩ		5.0	0.91	0.965	1.03	s
		10	0.92	0.98	1.04	
		15	0.93	0.99	1.06	
Pulse Width Match between circuits in	100	5.0	–	±1.0	±5.0	%
the same package.	$[(T_1 - T_2)/T_1]$	10	–	±1.0	±5.0	
C_X = 0.1 μF, R_X = 100 kΩ		15	–	±1.0	±5.0	

6. The formulas given are for the typical characteristics only at 25°C.
7. Data labelled “Typ” is not to be used for design purposes but is intended as an indication of the IC’s potential performance.

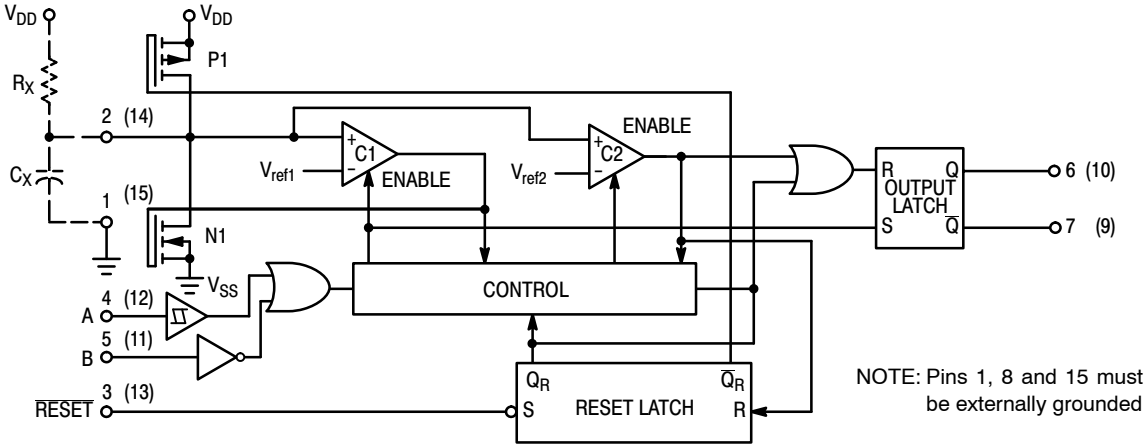


Figure 1. Logic Diagram (1/2 of Devlce Shown)

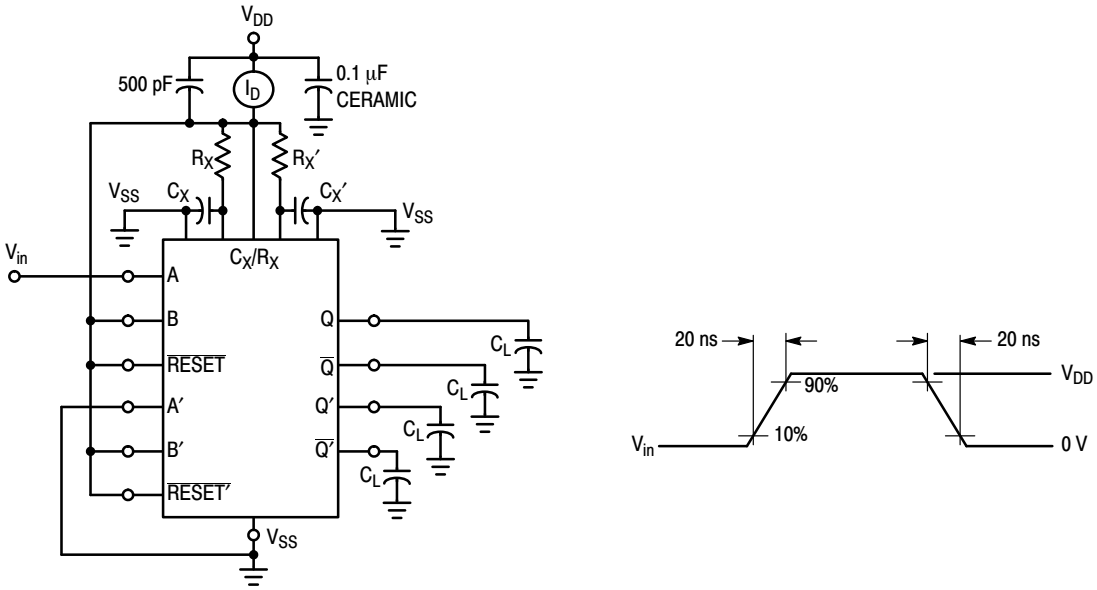
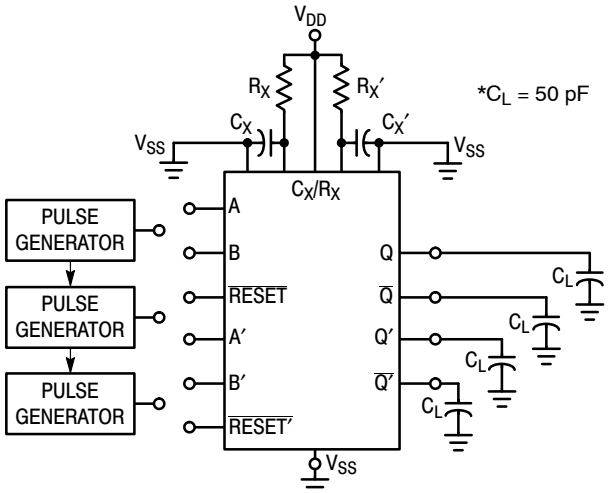


Figure 2. Power Dissipation Test Circuit and Waveforms



INPUT CONNECTIONS

Characteristics	$\overline{\text{Reset}}$	A	B
t_{PLH}, t_{PHL}, t_{TLH}, t_{THL}, T, t_{WH}, t_{WL}	V_{DD}	PG1	V_{DD}
t_{PLH}, t_{PHL}, t_{TLH}, t_{THL}, T, t_{WH}, t_{WL}	V_{DD}	V_{SS}	PG2
$t_{PLH(R)}$, $t_{PHL(R)}$, t_{WH}, t_{WL}	PG3	PG1	PG2

*Includes capacitance of probes, wiring, and fixture parasitic.

NOTE: Switching test waveforms for PG1, PG2, PG3 are shown In Figure 4.

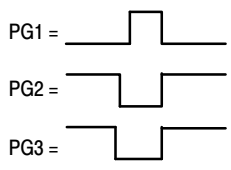


Figure 3. Switching Test Circuit

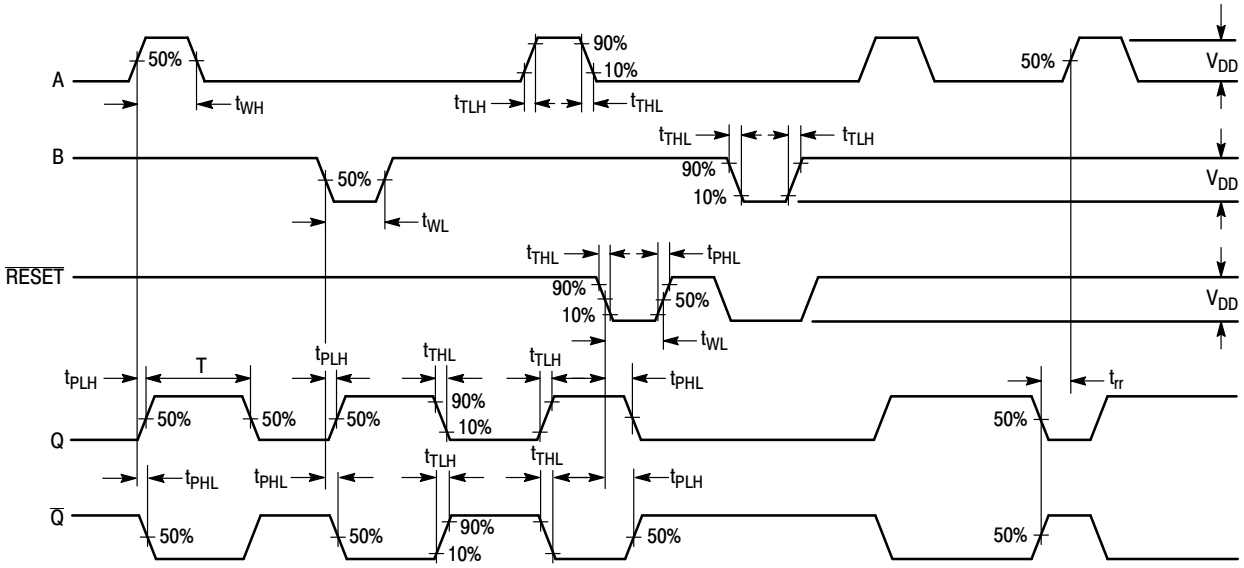


Figure 4. Switching Test Waveforms

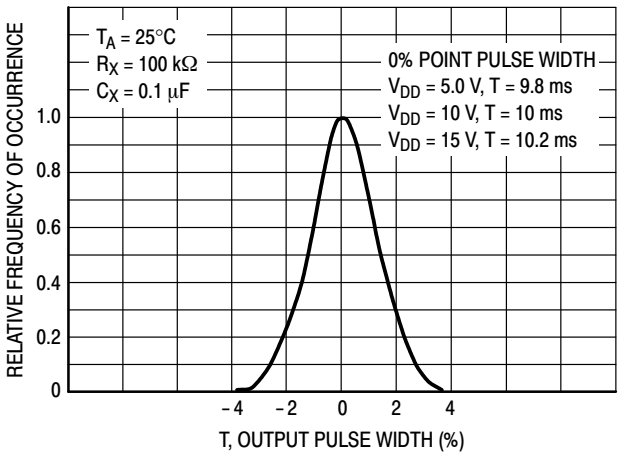


Figure 5. Typical Normalized Distribution of Units for Output Pulse Width

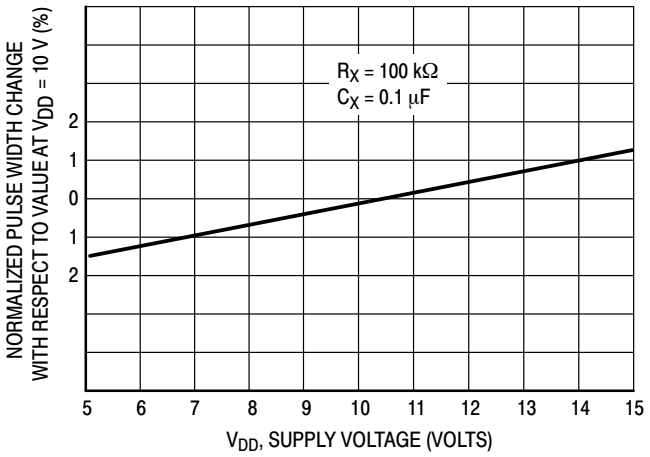


Figure 6. Typical Pulse Width Variation as a Function of Supply Voltage V_{DD}

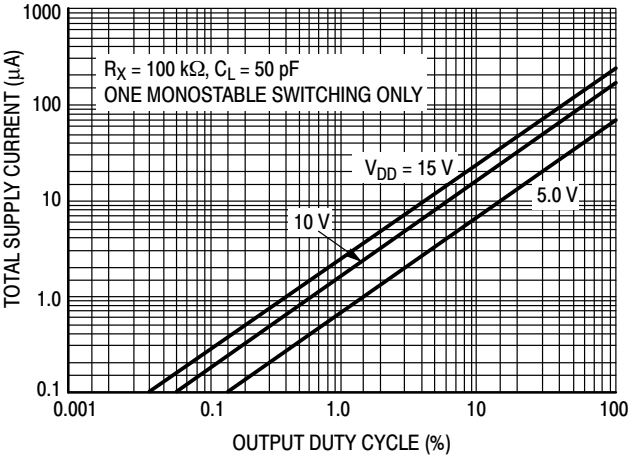


Figure 7. Typical Total Supply Current versus Output Duty Cycle

FUNCTION TABLE

Inputs			Outputs	
Reset	**A**	**B**	**Q**	**Q̄**
H	⌐	H	⌐¬	¬⌐
H	¬	⌐	⌐¬	¬⌐
H	⌐¬	L	Not Triggered	
H	H	⌐¬	Not Triggered	
H	L, H, ¬	H	Not Triggered	
H	L	L, H, ⌐	Not Triggered	
L	X	X	L	H
¬⌐	X	X	Not Triggered	

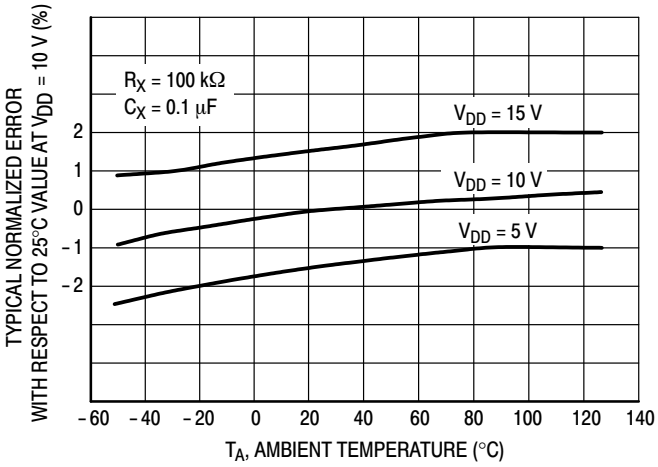


Figure 8. Typical Error of Pulse Width Equation versus Temperature

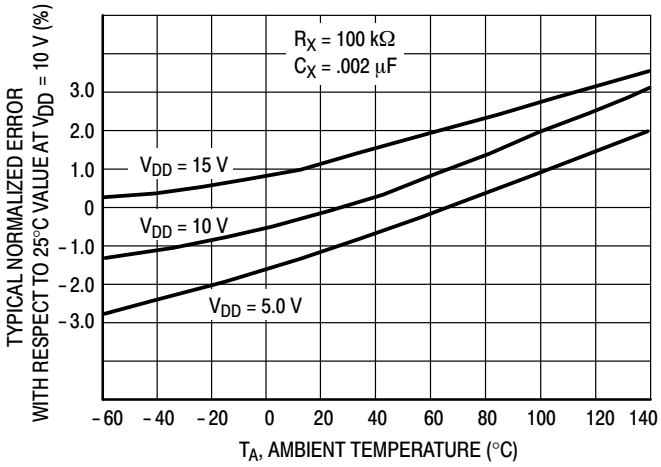


Figure 9. Typical Error of Pulse Width Equation versus Temperature

THEORY OF OPERATION

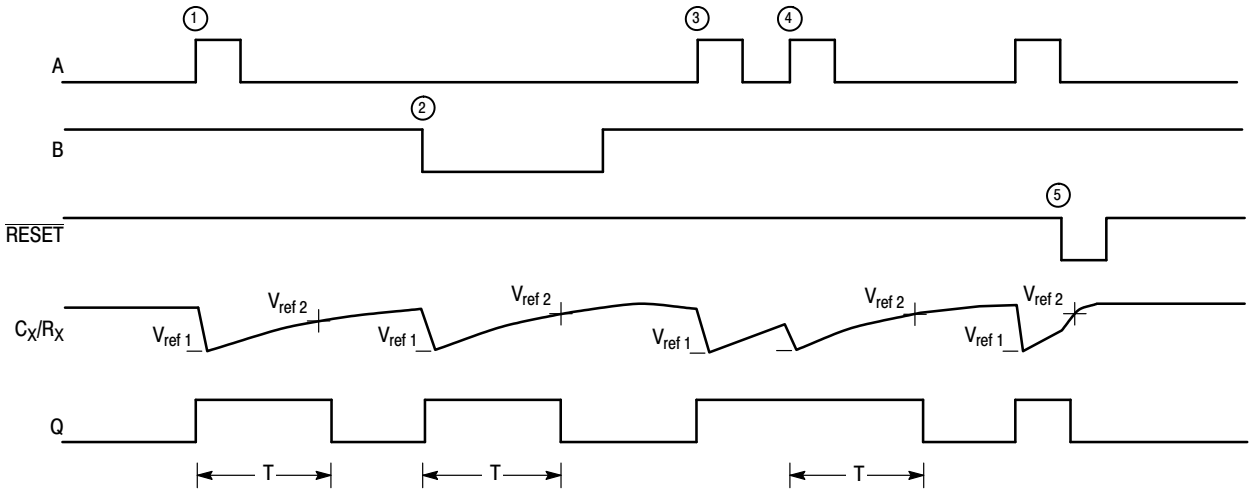


Figure 10. Timing Operation

TRIGGER OPERATION

The block diagram of the MC14538B is shown in Figure 1, with circuit operation following.

As shown in Figure 1 and 10, before an input trigger occurs, the monostable is in the quiescent state with the Q output low, and the timing capacitor C_X completely charged to V_{DD}. When the trigger input A goes from V_{SS} to V_{DD} (while inputs B and $\overline{\text{Reset}}$ are held to V_{DD}) a valid trigger is recognized, which turns on comparator C1 and N−channel transistor N1 ①. At the same time the output latch is set. With transistor N1 on, the capacitor C_X rapidly discharges toward V_{SS} until V_{ref1} is reached. At this point the output of comparator C1 changes state and transistor N1 turns off. Comparator C1 then turns off while at the same time comparator C2 turns on. With transistor N1 off, the capacitor C_X begins to charge through the timing resistor, R_X, toward V_{DD}. When the voltage across C_X equals $V_{ref\,2}$, comparator C2 changes state, causing the output latch to reset (Q goes low) while at the same time disabling comparator C2 ②. This ends at the timing cycle with the monostable in the quiescent state, waiting for the next trigger.

In the quiescent state, C_X is fully charged to V_{DD} causing the current through resistor R_X to be zero. Both comparators are "off" with total device current due only to reverse junction leakages. An added feature of the MC14538B is that the output latch is set via the input trigger without regard to the capacitor voltage. Thus, propagation delay from trigger to Q is independent of the value of C_X, R_X, or the duty cycle of the input waveform.

RETRIGGER OPERATION

The MC14538B is retriggered if a valid trigger occurs ③ followed by another valid trigger ④ before the Q output has returned to the quiescent (zero) state. Any retrigger, after the timing node voltage at pin 2 or 14 has begun to rise from $V_{ref\,1}$, but has not yet reached $V_{ref\,2}$, will cause an increase in output pulse width T. When a valid retrigger is initiated ④, the voltage at C_X/R_X will again drop to $V_{ref\,1}$ before progressing along the RC charging curve toward V_{DD}. The Q output will remain high until time T, after the last valid retrigger.

RESET OPERATION

The MC14538B may be reset during the generation of the output pulse. In the reset mode of operation, an input pulse on $\overline{\text{Reset}}$ sets the reset latch and causes the capacitor to be fast charged to V_{DD} by turning on transistor P1 ⑤. When the voltage on the capacitor reaches $V_{ref\,2}$, the reset latch will clear, and will then be ready to accept another pulse. It the $\overline{\text{Reset}}$ input is held low, any trigger inputs that occur will be inhibited and the Q and $\overline{Q}$ outputs of the output latch will not change. Since the Q output is reset when an input low level is detected on the $\overline{\text{Reset}}$ input, the output pulse T can be made significantly shorter than the minimum pulse width specification.

POWER−DOWN CONSIDERATIONS

Large capacitance values can cause problems due to the large amount of energy stored. When a system containing the MC14538B is powered down, the capacitor voltage may discharge from V_{DD} through the standard protection diodes at pin 2 or 14. Current through the protection diodes should be limited to 10 mA and therefore the discharge time of the V_{DD} supply must not be faster than (V_{DD}). (C)/(10 mA). For example, if V_{DD} = 10 V and C_X = 10 μF, the V_{DD} supply should discharge no faster than (10 V) x (10 μF)/(10 mA) = 10 ms. This is normally not a problem since power supplies are heavily filtered and cannot discharge at this rate.

When a more rapid decrease of V_{DD} to zero volts occurs, the MC14538B can sustain damage. To avoid this possibility use an external clamping diode, D_X, connected as shown in Fig. 11.

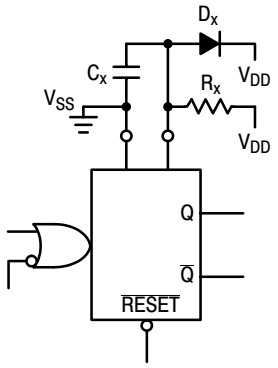


Figure 11. Use of a Diode to Limit Power Down Current Surge

TYPICAL APPLICATIONS

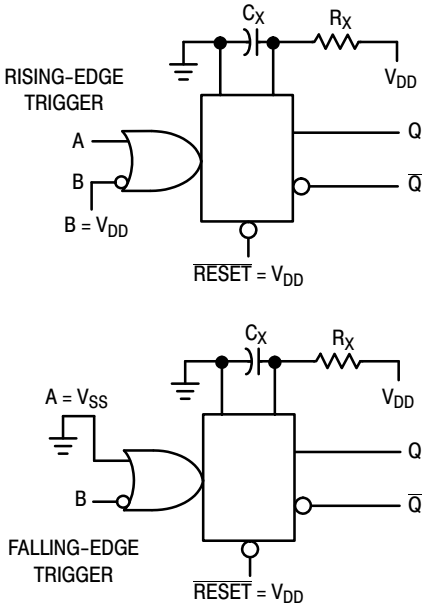


Figure 12. Retriggerable Monostables Circuitry

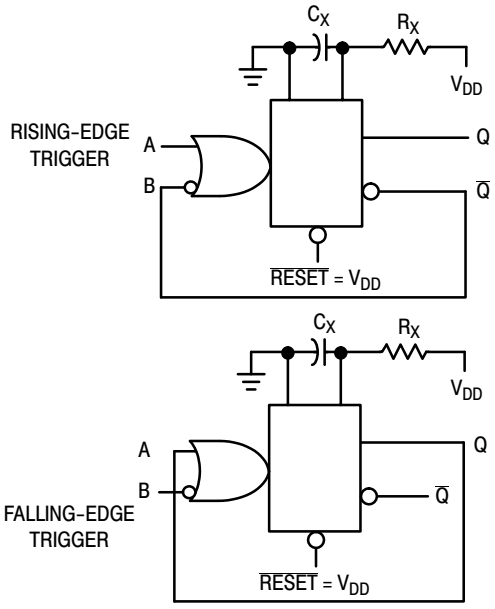


Figure 13. Non−Retriggerable Monostables Circuitry

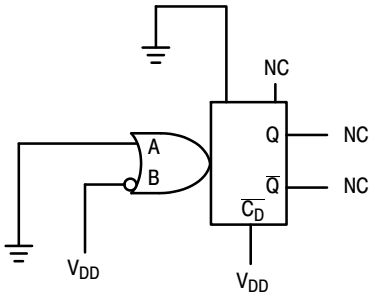


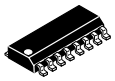
Figure 14. Connection of Unused Sections

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

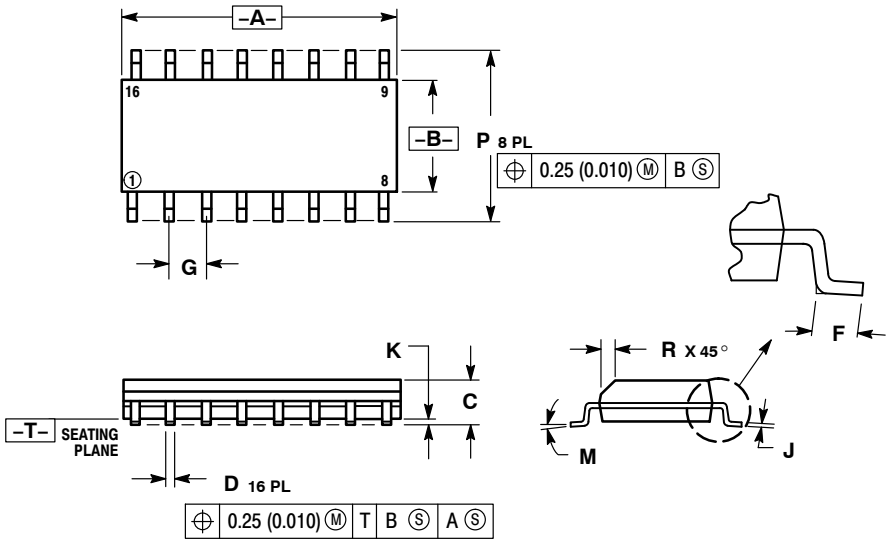
ON Semiconductor®

SOIC−16
CASE 751B−05
ISSUE K

DATE 29 DEC 2006



SCALE 1:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	9.80	10.00	0.386	0.393
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

STYLE 1:
PIN 1. COLLECTOR
2. BASE
3. EMITTER
4. NO CONNECTION
5. EMITTER
6. BASE
7. COLLECTOR
8. COLLECTOR
9. BASE
10. EMITTER
11. NO CONNECTION
12. EMITTER
13. BASE
14. COLLECTOR
15. EMITTER
16. COLLECTOR

STYLE 2:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION
4. CATHODE
5. CATHODE
6. NO CONNECTION
7. ANODE
8. CATHODE
9. CATHODE
10. ANODE
11. NO CONNECTION
12. CATHODE
13. CATHODE
14. NO CONNECTION
15. ANODE
16. CATHODE

STYLE 3:
PIN 1. COLLECTOR, DYE #1
2. BASE, #1
3. EMITTER, #1
4. COLLECTOR, #1
5. COLLECTOR, #2
6. BASE, #2
7. EMITTER, #2
8. COLLECTOR, #2
9. COLLECTOR, #3
10. BASE, #3
11. EMITTER, #3
12. COLLECTOR, #3
13. COLLECTOR, #4
14. BASE, #4
15. EMITTER, #4
16. COLLECTOR, #4

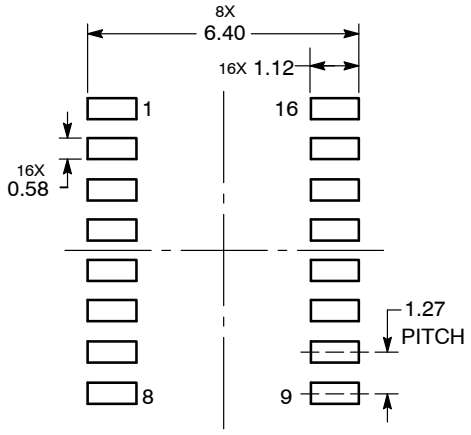
STYLE 4:
PIN 1. COLLECTOR, DYE #1
2. COLLECTOR, #1
3. COLLECTOR, #2
4. COLLECTOR, #2
5. COLLECTOR, #3
6. COLLECTOR, #3
7. COLLECTOR, #4
8. COLLECTOR, #4
9. BASE, #4
10. EMITTER, #4
11. BASE, #3
12. EMITTER, #3
13. BASE, #2
14. EMITTER, #2
15. BASE, #1
16. EMITTER, #1

STYLE 5:
PIN 1. DRAIN, DYE #1
2. DRAIN, #1
3. DRAIN, #2
4. DRAIN, #2
5. DRAIN, #3
6. DRAIN, #3
7. DRAIN, #4
8. DRAIN, #4
9. GATE, #4
10. SOURCE, #4
11. GATE, #3
12. SOURCE, #3
13. GATE, #2
14. SOURCE, #2
15. GATE, #1
16. SOURCE, #1

STYLE 6:
PIN 1. CATHODE
2. CATHODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE
7. CATHODE
8. CATHODE
9. ANODE
10. ANODE
11. ANODE
12. ANODE
13. ANODE
14. ANODE
15. ANODE
16. ANODE

STYLE 7:
PIN 1. SOURCE N-CH
2. COMMON DRAIN (OUTPUT)
3. COMMON DRAIN (OUTPUT)
4. GATE P-CH
5. COMMON DRAIN (OUTPUT)
6. COMMON DRAIN (OUTPUT)
7. COMMON DRAIN (OUTPUT)
8. SOURCE P-CH
9. SOURCE P-CH
10. COMMON DRAIN (OUTPUT)
11. COMMON DRAIN (OUTPUT)
12. COMMON DRAIN (OUTPUT)
13. GATE N-CH
14. COMMON DRAIN (OUTPUT)
15. COMMON DRAIN (OUTPUT)
16. SOURCE N-CH

SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

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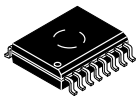
DESCRIPTION:	SOIC−16	PAGE 1 OF 1

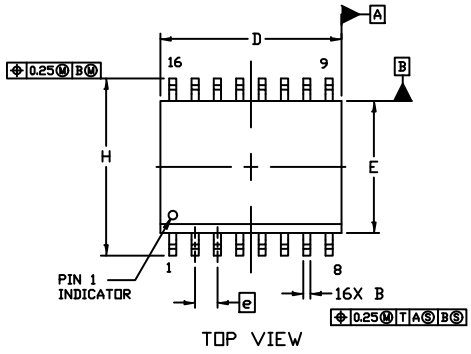
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

SOIC−16 WB
CASE 751G
ISSUE E

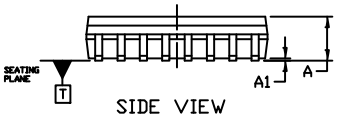
DATE 08 OCT 2021



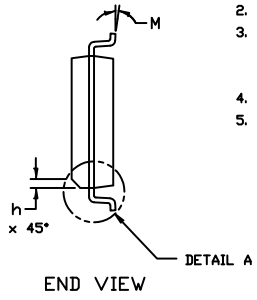
1
SCALE 1:1



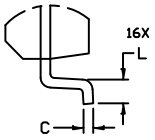
TOP VIEW



SIDE VIEW



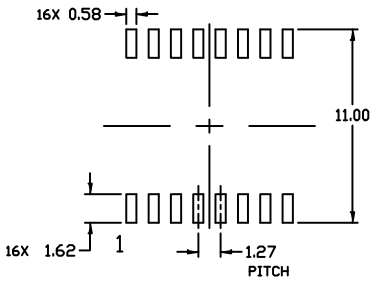
END VIEW



DETAIL A
2X SCALE

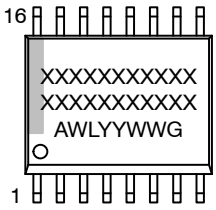
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION OR FLASH TO BE 0.15 PER SIDE.

	MILLIMETERS	
DIM	MIN.	MAX.
A	2.35	2.65
A1	0.10	0.25
B	0.35	0.49
C	0.23	0.32
D	10.15	10.45
E	7.40	7.60
e	1.27 BSC	
H	10.05	10.55
h	0.53 REF	
L	0.50	0.90
M	0°	7°



RECOMMENDED
MOUNTING FOOTPRINT

GENERIC
MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
WL = Wafer Lot
YY = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

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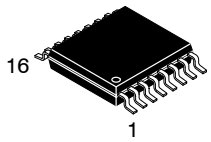
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

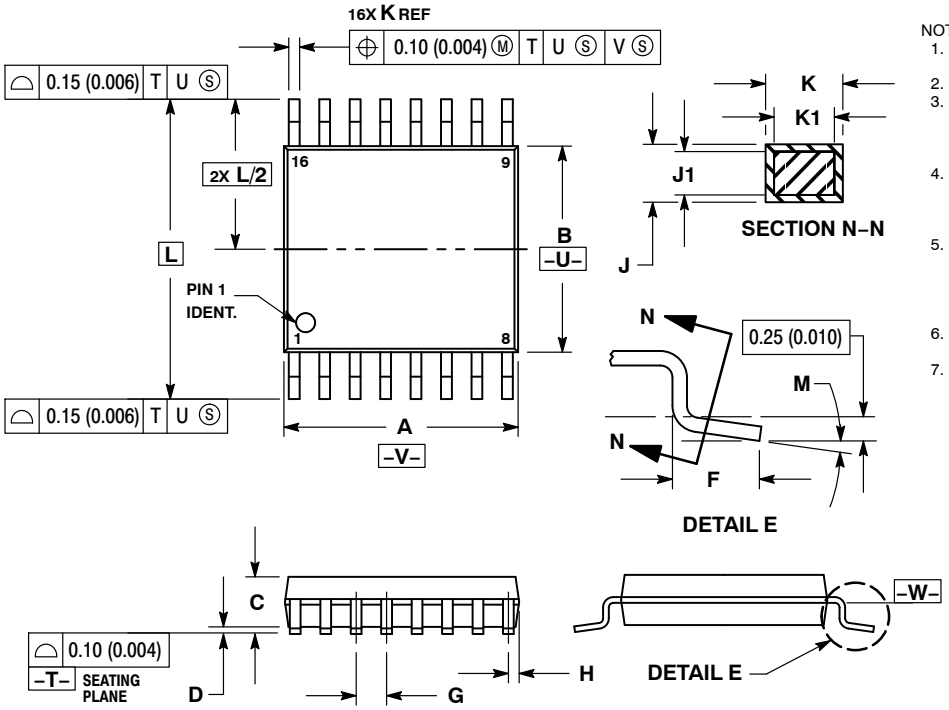
ON Semiconductor®



SCALE 2:1

TSSOP−16
CASE 948F−01
ISSUE B

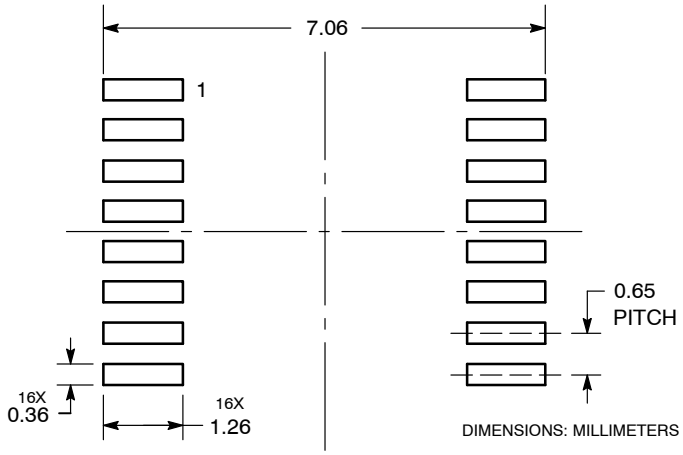
DATE 19 OCT 2006



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE −W−.

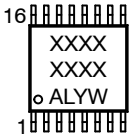
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	−−−	1.20	−−−	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

GENERIC MARKING DIAGRAM*



XXXX	= Specific Device Code
A	= Assembly Location
L	= Wafer Lot
Y	= Year
W	= Work Week
G or ▪	= Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

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